	1 A A A A A A A A A A A A A A A A A A A
ΡΛΝ	JIT
	SEMI
	CONDUCTOR

30V N-Channel Enhancement Mode MOSFET

Voltage

Current 61 A

Features

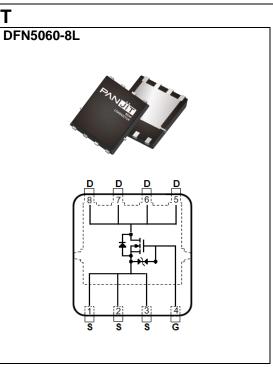
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@20A < 6m\Omega$
- R_{DS(ON)}, V_{GS}@4.5V, I_D@10A<9.5mΩ

30 V

- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN5060-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETE	R	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	30	
Gate-Source Voltage		V _{GS}	±20	V
Constitution Duration Common (Note 3)	Tc=25°C		61	
Continuous Drain Current ^(Note 3)	Tc=100°C	ID	43	А
Pulsed Drain Current ^(Note 1)	Tc=25°C	I _{DM}	244	
De la Dischartier	Tc=25°C		31.3	14/
Power Dissipation	Tc=100°C	Po	15.6	W
Continuous Drain Curront(Note 4)	T _A =25°C		19.3	
Continuous Drain Current ^(Note 4)	T _A =70°C	ID	16	— A
Devue Dissis stien	T _A =25°C	D _	3.3	14/
Power Dissipation	T _A =70°C	Po	2.3	W
Single Pulse Avalanche Energy ^(Note 5)		E _{AS}	49	mJ
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C
Thermal Decistores (Note 4)	Junction to Case	$R_{ extsf{ heta}JC}$	4.2	°C/W
Thermal Resistance ^(Note 4)	Junction to Ambient	R _{θJA}	45	C/vv



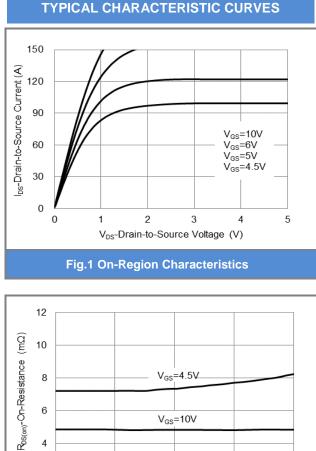
Electrical Characteristics (TA=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	Vgs=0V, Id=250uA	30	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.3	1.8	2.5		
Ducia Course On State Decistance		V _{GS} =10V, I _D =20A	-	4.8	6		
Drain-Source On-State Resistance R _{DS(on)}		V _{GS} =4.5V, I _D =10A		7.3	9.5	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	uA	
Osta Caura la skans Ourrant		V _{GS} =±20V, V _{DS} =0V	-	-	±10		
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±1	uA	
Dynamic ^(Note 6)	1	1		-	•		
Total Gate Charge	Qg		-	11	-	nC	
Gate-Source Charge	Qgs	V _{DS} =24V, I _D =20A,	-	2.4	-		
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	1.3	-		
Input Capacitance	Ciss		-	710	-		
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V,	-	346	-	pF	
Reverse Transfer Capacitance	Crss	f=1MHz	-	30	-		
Gate resistance	Rg	f=1MHz	-	1.7	-	Ω	
Turn-On Delay Time	td _(on)		-	9	-		
Turn-On Rise Time	tr	V _{DS} =24V, I _D =20A,	-	2	-		
Turn-Off Delay Time	td _(off)	V _{GS} =10V, R _G =3Ω	-	20	-	ns	
Turn-Off Fall Time	tf		-	7	-		
Drain-Source Diode	•						
Diode Forward Current	I _S	T _c =25°C	-	-	61		
Pulsed Diode Forward Current	I _{SM}	1C=20 C	-	-	244	A	
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V	-	0.85	1.1	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =20A	-	14	-	ns	
Reverse Recovery Charge	Qrr	dls/dt=100A/us	-	13	-	nC	

NOTES :

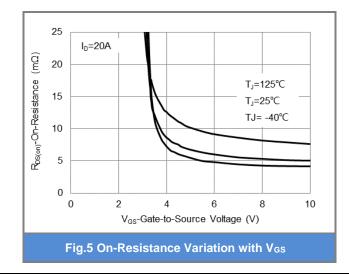
- 1. Pulse width100us, Duty cycle<2%.</td>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an $R_{\theta JC}$ =4.2°C/W.
- 4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS}=14A, V_{DD}=30V, V_{GS}=10V, Starting T_J=25^{\circ}C.
- 6. Guaranteed by design, not subject to production testing.





6 V_{GS}=10V 4 2 0 15 30 45 60 I_{DS}-Drain-to-Source Current (A)

Fig.3 On-Resistance vs. Drain Current



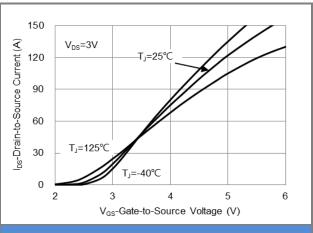


Fig.2 Transfer Characteristics

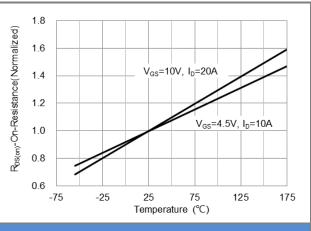
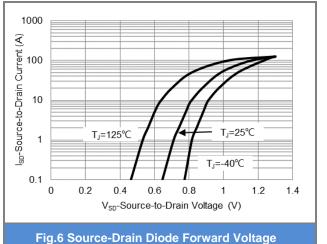
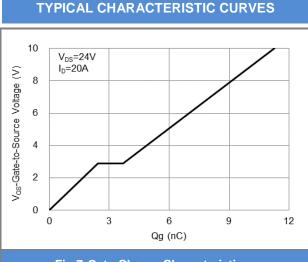


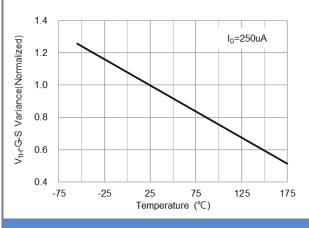
Fig.4 On-Resistance vs. Junction temperature



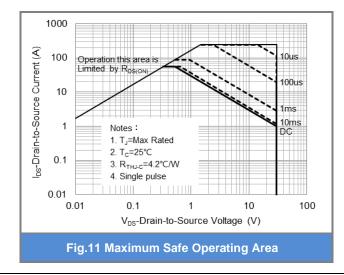


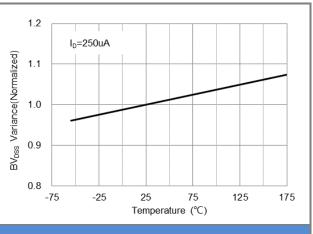














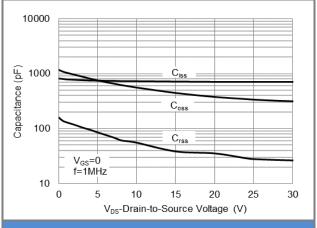
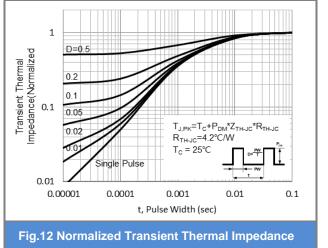


Fig.10 Capacitance vs. Drain-Source Voltage

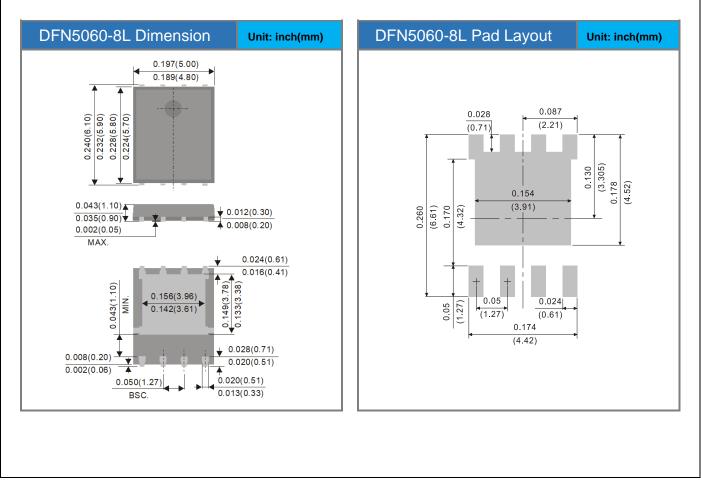




Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ5528-AU	DFN5060-8L	3K pcs / 13" reel	Q5528	

Packaging Information & Mounting Pad Layout





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